



MICROCIRCUIT DATA SHEET

MNDS90C032-X-RH REV 1B1

Original Creation Date: 04/14/00
Last Update Date: 08/15/03
Last Major Revision Date:

**LVDS Quad CMOS Differential Line Receiver: ALSO
AVAILABLE GUARANTEED TO 50K RAD(SI) TESTED TO
MIL-STD-883, METHOD 1019.5**

General Description

The DS90C032 is a quad differential line receiver designed for applications requiring low power dissipation and high data rates.

The DS90C032 accepts low voltage differential input signal and translates them to CMOS (TTL compatible) output levels. The receiver supports a TRI-STATE function that may be used to multiplex outputs.

The DS90C032 and companion line driver (DS90C031) provide a new alternative to high power pseudo-ECL devices for high speed point to point interfaces.

In addition, the DS90C032A provides power-off high impedance LVDS inputs. This feature assures minimal loading effect on the LVDS bus lines when VCC is not present.

Industry Part Number

DS90C032

Prime Die

DS90C032

NS Part Numbers

DS90C032E-QML
DS90C032W-QML
DS90C032W-QMLV
DS90C032WG-QML
DS90C032WG-QMLV
DS90C032WGLQMLV
DS90C032WLQMLV

Controlling Document

SEE FEATURES SECTION

Processing

MIL-STD-883, Method 5004

Quality Conformance Inspection

MIL-STD-883, Method 5005

Subgrp Description

		Temp (°C)
1	Static tests at	+25
2	Static tests at	+125
3	Static tests at	-55
4	Dynamic tests at	+25
5	Dynamic tests at	+125
6	Dynamic tests at	-55
7	Functional tests at	+25
8A	Functional tests at	+125
8B	Functional tests at	-55
9	Switching tests at	+25
10	Switching tests at	+125
11	Switching tests at	-55

Features

- High impedance LVDS inputs with power-off
- Accepts small swing (330 mV) differential signal levels.
- Low power dissipation.
- Low differential skew.
- Low chip to chip skew
- Mil operating temperature range
- Pin compatible with DS26C32A.
- Compatible with IEEE P1596.3 SCI LVDS draft standard
- Typical Rise/Fall time is TBD

CONTROLLING DOCUMENTS:

DS90C032E-QML	5962-9583401Q2A
DS90C032W-QML	5962-9583401QFA
DS90C032W-QMLV	5962-9583401VFA
DS90C032WG-QML	5962-9583401QZA
DS90C032WG-QMLV	5962-9583401VZA
DS90C032WGLQMLV	5962-9583401VZA
DS90C032WLQMLV	5962L9583401VFA

(Absolute Maximum Ratings)

(Note 1)

Supply Voltage (Vcc)	-0.3 to +6V
Input Voltage (RIN+, RIN-)	-0.3 to (Vcc+0.3V)
Enable Input Voltage (EN, EN*)	-0.3 to (Vcc+0.3V)
Output Voltage (ROUT)	-0.3 to (Vcc+0.3V)
Storage Temperature Range (Tstg)	-65 C ≤ Ta ≤ + 150 C
Lead Temperature Soldering 4 seconds	260 C
Maximum Package Power Dissipation @ +25C (Note 2)	
20 PIN LCC (E Pkg)	1830 mW
16 PIN CERPAK (W Pkg)	1400 mW
16 PIN CERAMIC SOIC (WG Pkg)	TBD
Thermal Resistance. (Theta JA)	
20 PIN LCC (E Pkg)	82 C/W
16 PIN CERPAK (W Pkg)	148 C/W
16 PIN CERAMIC SOIC (WG Pkg)	TBD
Thermal Resistance. (Theta JC)	
20 PIN LCC (E Pkg).	20 C/W
16 PIN CERPAK (W Pkg)	20 C/W
16 PIN CERAMIC SOIC (WG Pkg)	TBD
ESD Rating.	2000 Volts.

Note 1: Absolute Maximum Ratings are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Derate (E Pkg) @ 12.2mW/C above +25C. Derate (W Pkg) @ 6.8 mW/C above +25C.

Recommended Operating Conditions

Operating Voltage (Vcc)	4.5V to 5.5V
Operating Temperature Range (Ta)	-55C to +125C
Receiver Input Voltage	GND to 2.4V

Electrical Characteristics

DC PARAMETERS: (SEE NOTE 4)

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN-NAME	MIN	MAX	UNIT	SUB-GROUPS
VTL	Differential Input Low Threshold	V _{cm} = +1.2V	1	RIN+, RIN-		-100	mV	1, 2, 3
VTH	Differential Input High Threshold	V _{cm} = +1.2V	1	RIN+, RIN-		100	mV	1, 2, 3
IIN	Input Current	V _{CC} =5.5V, V _{in} = 2.4V		RIN+, RIN-		± 10	uA	1, 2, 3
		V _{CC} = 5.5V, V _{in} = 0		RIN+, RIN-		± 10	uA	1, 2, 3
		V _{CC} = 0.0V, V _{in} = 2.4V		RIN+, RIN-		± 10	uA	1, 2, 3
		V _{CC} = 0.0V, V _{in} = 0.0V		RIN+, RIN-		± 10	uA	1, 2, 3
VOH	Output High Voltage	V _{CC} = 4.5V, I _{OH} = -0.4 mA, V _{ID} = 200mV		ROUT	3.8		V	1, 2, 3
VOL	Output Low Voltage	V _{CC} = 4.5, I _{OL} = 2 mA, V _{ID} = -200mV		ROUT		0.3	V	1, 2, 3
IOS	Output Short Circuit Current	Enabled, V _{out} = 0V		ROUT	-15	-100	mA	1, 2, 3
IOZ	Output TRI-STATE Current	Disabled, V _{out} = 0V or V _{CC}		ROUT		± 10	uA	1, 2, 3
VIH	Input High Voltage		1	EN, EN*	2.0		V	1, 2, 3
VIL	Input Low Voltage		1	EN, EN*		0.8	V	1, 2, 3
II	Input Current	V _{CC} = 5.5V		EN, EN*		± 10	uA	1, 2, 3
VCL	Input Clamp Voltage	I _{CL} = -18mA		EN, EN*		-1.5	V	1, 2, 3
Icc	No Load Supply Current	EN, EN* = V _{CC} or GND, Inputs Open		V _{CC}		11	mA	1, 2, 3
		EN, EN* = 2.4 or 0.5, Inputs Open		V _{CC}		11	mA	1, 2, 3
IccZ	No Load Supply Current Receivers Disabled	EN = GND, EN* = V _{CC} , Inputs Open		V _{CC}		11	mA	1, 2, 3

Electrical Characteristics

AC PARAMETERS: (SEE NOTE 4)

(The following conditions apply to all the following parameters, unless otherwise specified.)
 AC: VCC = 4.5V/5.0V/5.5V, CL = 20pF

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN-NAME	MIN	MAX	UNIT	SUB-GROUPS
tPHLD	Differential Propagation Delay High to Low	Vid = 200mV, Input pulse = 1.1V to 1.3V, Vin = 1.2V (0 differential) to Vout = 1/2 Vcc			1.0	8	ns	9, 10, 11
tPLHD	Differential Propagation Delay Low to High	Vid = 200mV, Input pulse = 1.1V to 1.3V, Vin = 1.2V (0V differential) to Vout = 1/2 Vcc			1.0	8	ns	9, 10, 11
tSKD	Differential Skew tPHLD-tPLHD	CL = 20pF, Vid = 200mV				3	ns	9, 10, 11
tSK1	Channel to Channel Skew	CL = 20pF, Vid = 200mV	2			3	ns	9, 10, 11
tSK2	Chip to Chip Skew	CL = 20pF, Vid = 200mV	3			7	ns	9, 10, 11
tPLZ	Disable Time Low to Z	Input pulse = 0V to 3.0V, Vin = 1.5V, Vout = Vol+0.5V, Rload = 1k Ohm to VCC				20	ns	9, 10, 11
tPHZ	Disable Time High to Z	Input pulse = 0V to 3.0V, Vin = 1.5V, Vout = Voh-0.5V, Rload = 1k Ohm to GND				20	ns	9, 10, 11
tPZH	Enable Time Z to High	Input pulse = 0V to 3.0V, Vin = 1.5V, Vout = 50%, Rload = 1k Ohm to GND				20	ns	9, 10, 11
tPZL	Enable Time Z to Low	Input pulse = 0V to 3.0V, Vin = 1.5V, Vout = 50%, Rload = 1k Ohm to VCC				20	ns	9, 10, 11

AC/DC PARAMETERS: POST RADIATION LIMITS (SEE NOTE 4)

Icc	No Load Supply Current	EN, EN* = Vcc or GND, Inputs Open				20	mA	1
		EN, EN* = 2.4 or 0.5, Inputs Open				20	mA	1
Iccz	No Load Supply Current Receivers Disabled	EN = GND, EN* = Vcc, Inputs Open				20	mA	1

Note 1: Tested during VOH/VOL tests.

Note 2: Channel to Channel Skew is defined as the difference between the propagation delay of one channel and that of the others on the same chip with an event on the inputs.

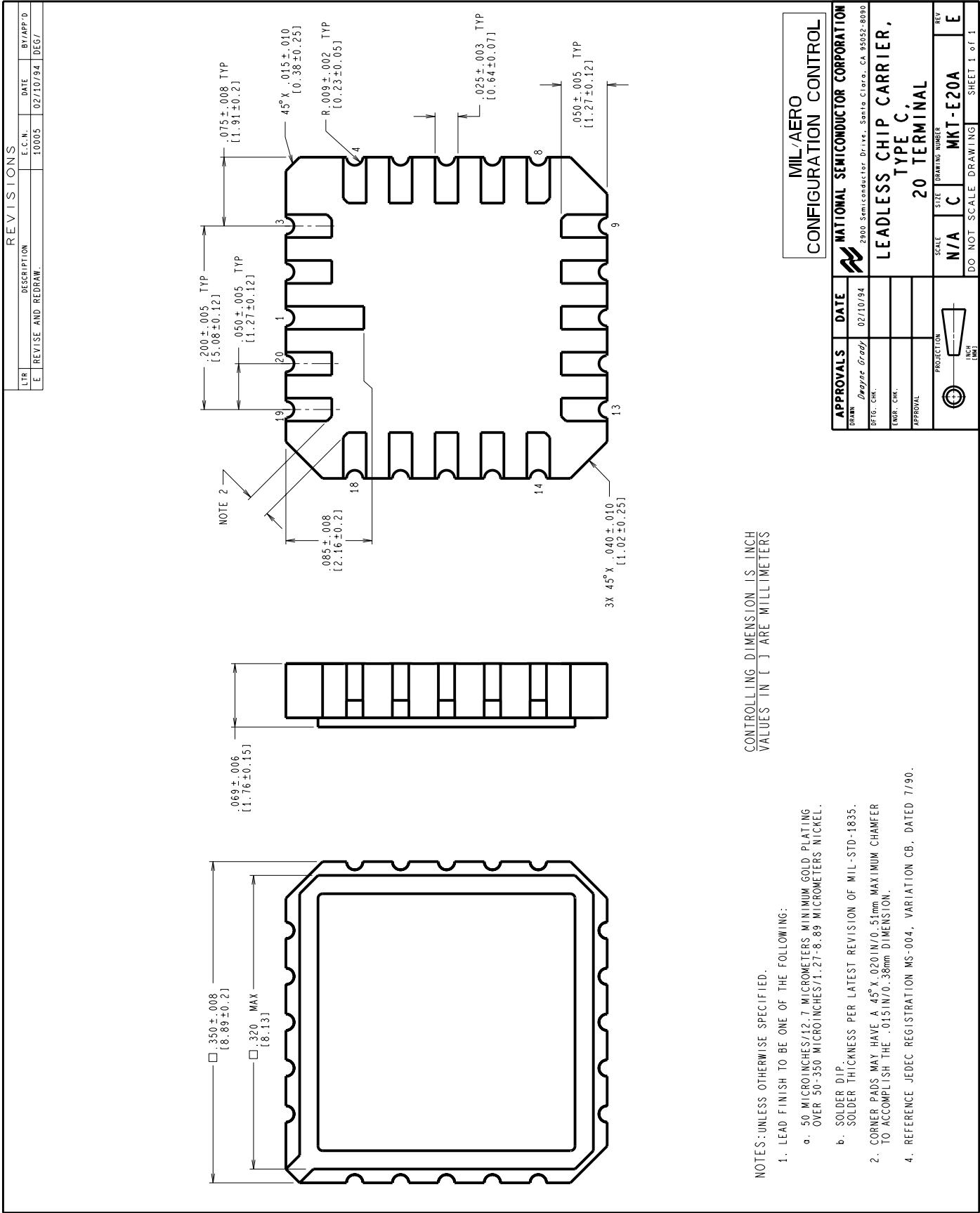
Note 3: Chip to Chip Skew is defined as the difference between the minimum and maximum specified differential propagation delays.

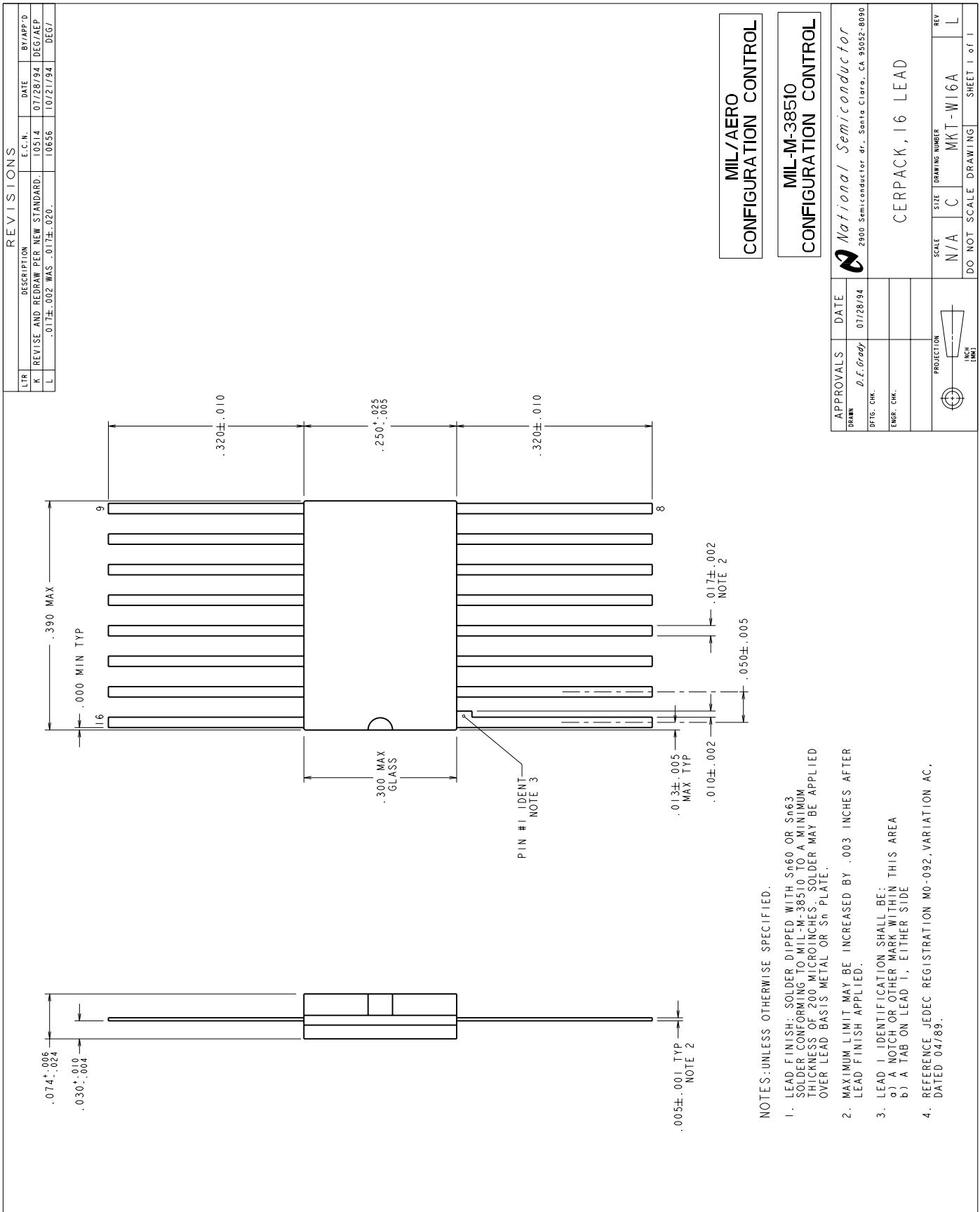
Note 4: Pre and post irradiation limits are identical to those listed under AC and DC electrical characteristics except as listed in the Post Radiation Limits Table (IF APPLICABLE). Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified.

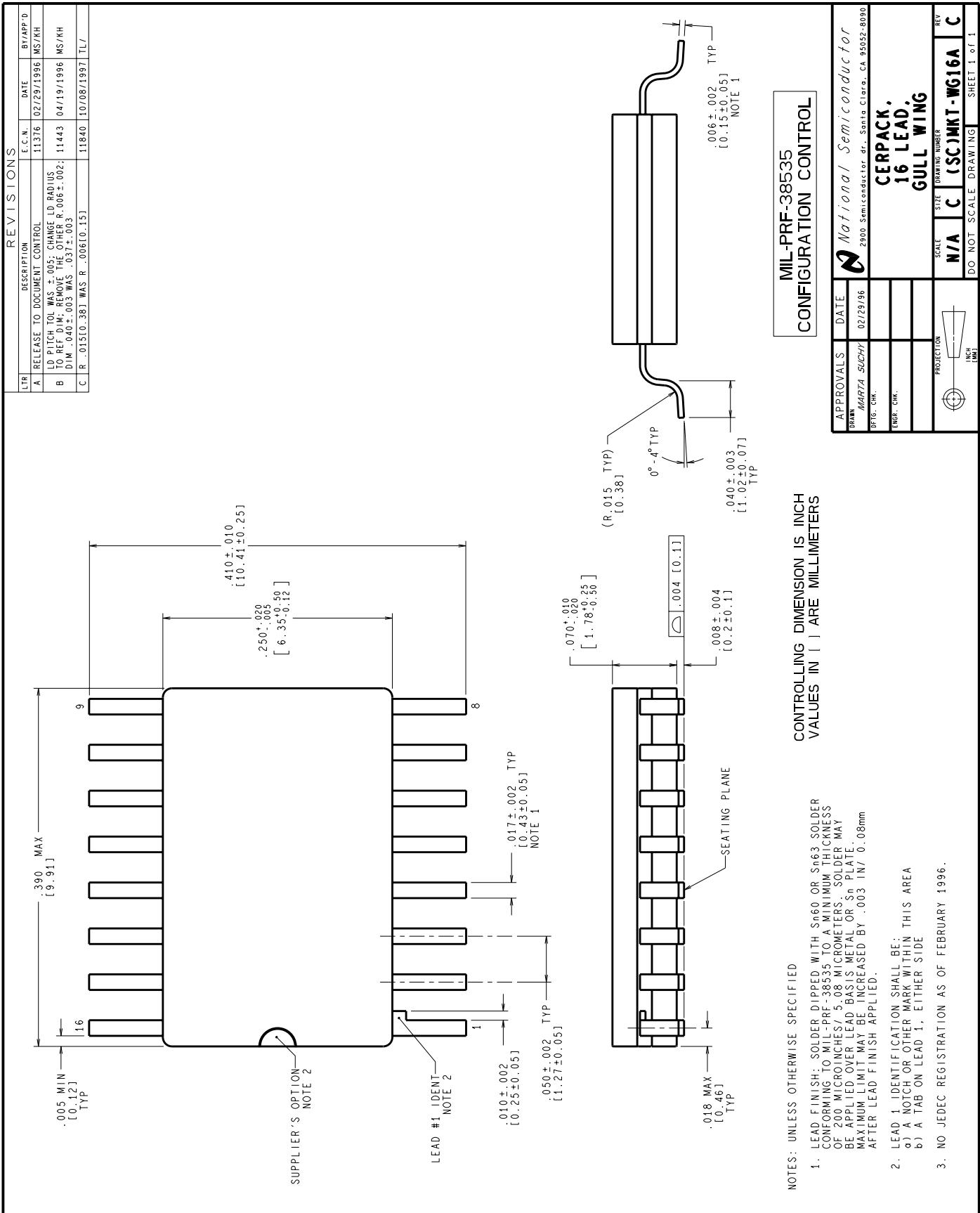
Graphics and Diagrams

GRAPHICS#	DESCRIPTION
E20ARE	LCC (E), TYPE C, 20 TERMINAL(P/P DWG)
W16ARL	CERPACK (W), 16 LEAD (P/P DWG)
WG16ARC	CERAMIC SOIC (WG), 16 LEAD (P/P DWG)

See attached graphics following this page.







Revision History

Rev	ECN #	Rel Date	Originator	Changes
0A0	M0003844	06/21/02	Rose Malone	Initial MDS Release
1A1	M0004012	08/15/03	Rose Malone	Update MDS: MNDS90C032-X-RH, Rev. 0A0 to MNDS90C032-X-RH, Rev. 1A1. Added reference to WG pkg to Main Table, Features Section, Absolute Maximum Section and Graphics Section.
1B1	M0004182	08/15/03	Rose Malone	Update MDS: MNDS90C032-X-RH, Rev. 1A1 to 1B1. MDS enhancements: Additional verbage to the general description, Main Table and Added new bullet to the Features Section.